

## Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

$V_{RRM}$	650V
$I_F (T_c = 104.5^\circ\text{C})$	15A
$Q_c$	32nC

## Benefits

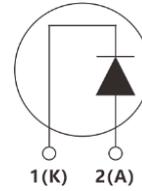
- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

## Applications

- SMPS, PFC
- Solar application, UPS, EV/HEV
- Motor drives, Wind turbine, Rail traction



TO-220F(SG)



Inner Circuit



G = GPT  
4 = Gen4  
S = SiC Schottky Diode  
065 = Voltage Rating 650V  
15 = Current Rating 15A  
HT = TO-220F(SG)  
DDDDDD = Traceable Code





**Maximum Ratings** (at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	650	V
Surge Peak Reverse Voltage	$V_{RSM}$	650	V
Continuous Forward Current $T_c = 25\text{ }^\circ\text{C}$ $T_c = 104.5\text{ }^\circ\text{C}$	$I_F$	23.2 15	A
Repetitive Peak Forward Surge Current $T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$ , Half Sine Pulse, $D = 0.1$ , 1000Cycle	$I_{FRM}$	50	A
Non-Repetitive Forward Surge Current $T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$ , Half Sine Pulse	$I_{FSM}$	100	A
$i^2t$ Value $T_c = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ms}$ , Half Sine Pulse	$\int i^2 dt$	50	$\text{A}^2\text{s}$
Power Dissipation $T_c = 25\text{ }^\circ\text{C}$ $T_c = 110\text{ }^\circ\text{C}$	$P_{tot}$	68 30	W
Operating Junction Range	$T_J$	-55 to +175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +175	$^\circ\text{C}$
Mounting Torque, M3 Screw	M	1	Nm

**Electrical Characteristics** (at  $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
DC Blocking Voltage	$V_{DC}$		650	-	-	V
Forward Voltage	$V_F$	$I_F = 15\text{A}$ $T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$T_J = 175^\circ\text{C}$	-	2.1	2.5	
Reverse Current	$I_R$	$V_R = 650\text{V}$ $T_J = 25^\circ\text{C}$	-	0.35	50	$\mu\text{A}$
		$T_J = 175^\circ\text{C}$	-	2.4	100	
Total Capacitance	C	$f = 1\text{MHz}$ $V_R = 0\text{V}$	-	618	-	pF
		$V_R = 200\text{V}$	-	62	-	
		$V_R = 400\text{V}$	-	56	-	
Total Capacitive Charge	$Q_C$	$V_R = 400\text{V}$ $T_J = 25^\circ\text{C}$	-	32	-	nC
Capacitance Stored Energy	$E_C$	$V_R = 400\text{V}$	-	8	-	$\mu\text{J}$

**Thermal Characteristics**

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
Thermal Resistance, junction-case	$R_{th(j-c)}$		-	2.2	-	$^\circ\text{C}/\text{W}$

Typical Characteristics Curves

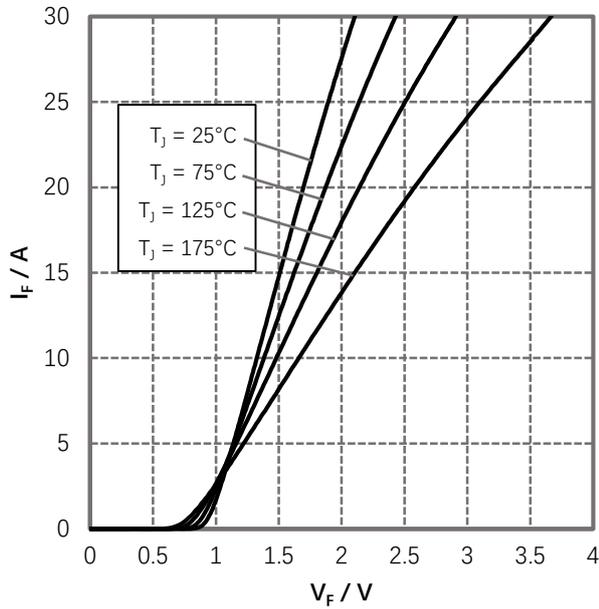


Figure 1. Forward Characteristics

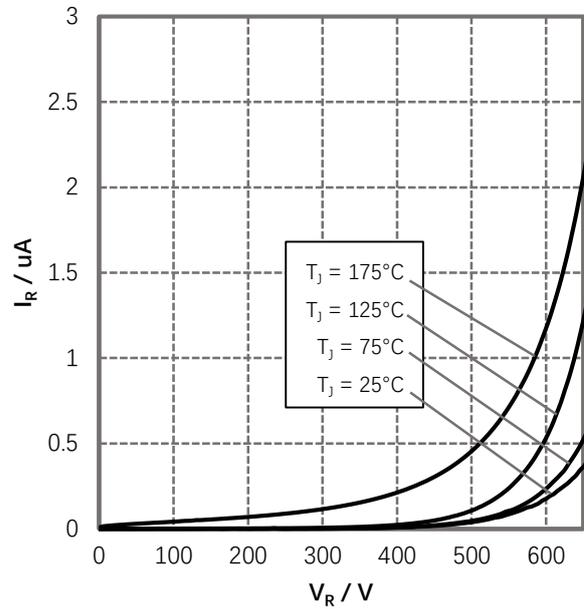


Figure 2. Reverse Characteristics

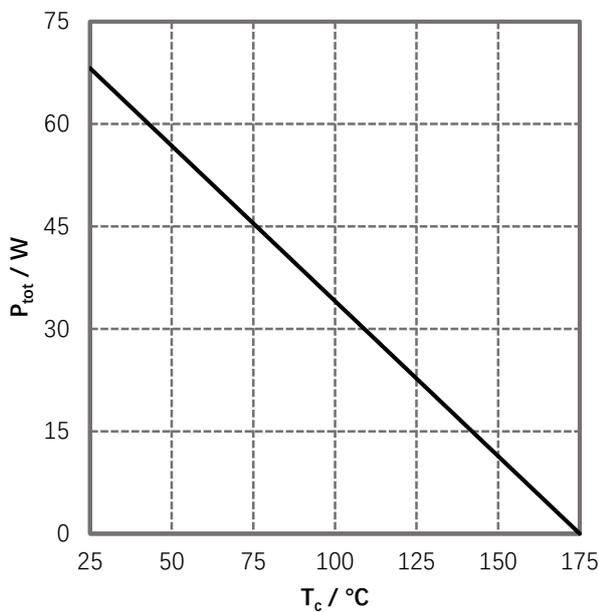


Figure 3. Power Derating

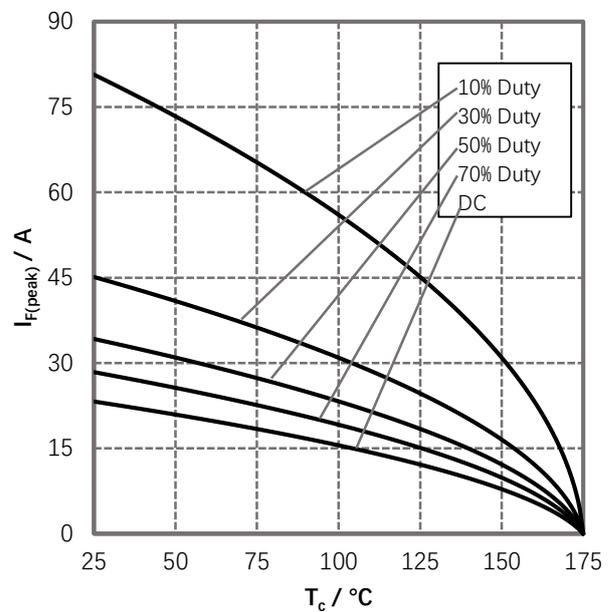


Figure 4. Current Derating  
Valid for switching of above 20kHz,  
excluding D.C. curve



### Typical Characteristics Curves

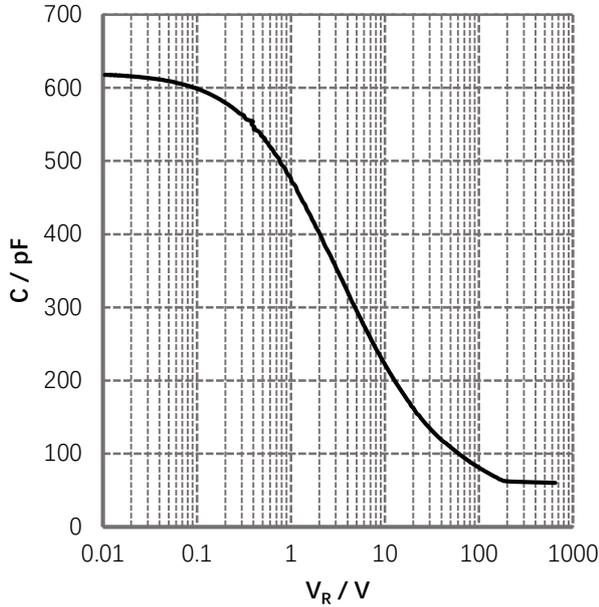


Figure 5. Capacitance vs. Reverse Voltage

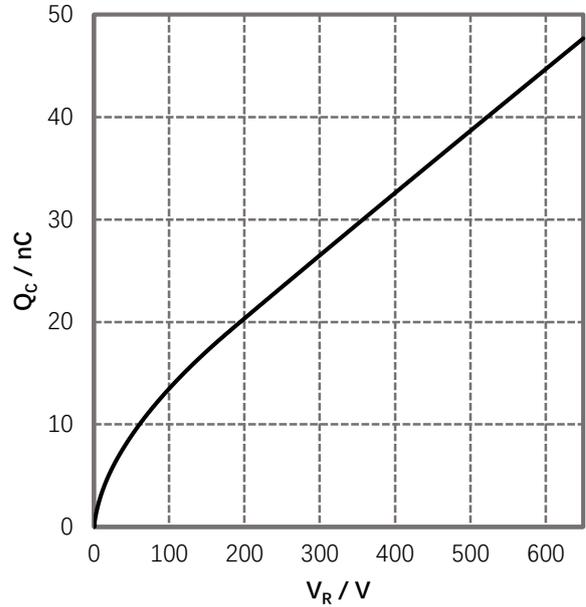


Figure 6. Reverse Charge vs. Reverse Voltage

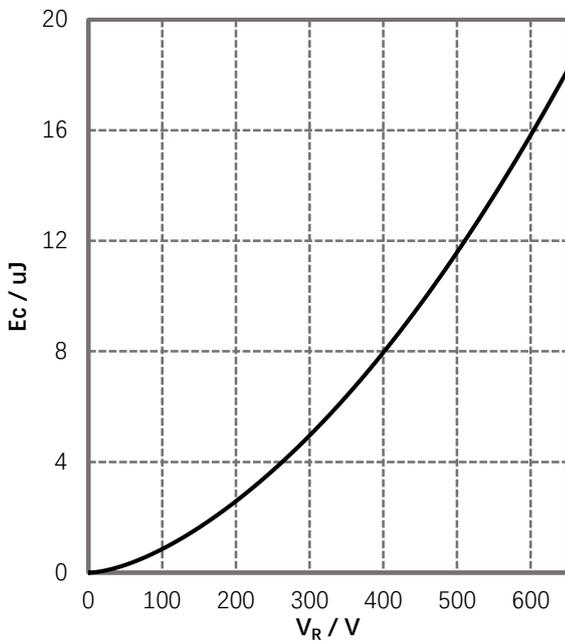


Figure 7. Capacitance Stored Energy

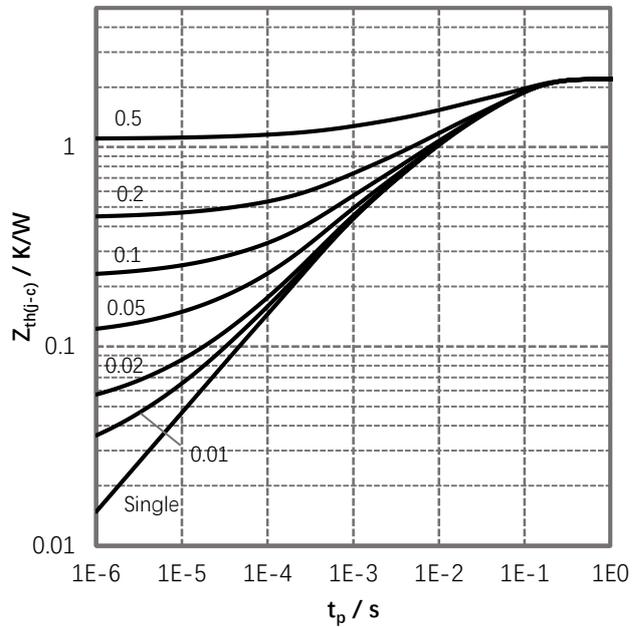
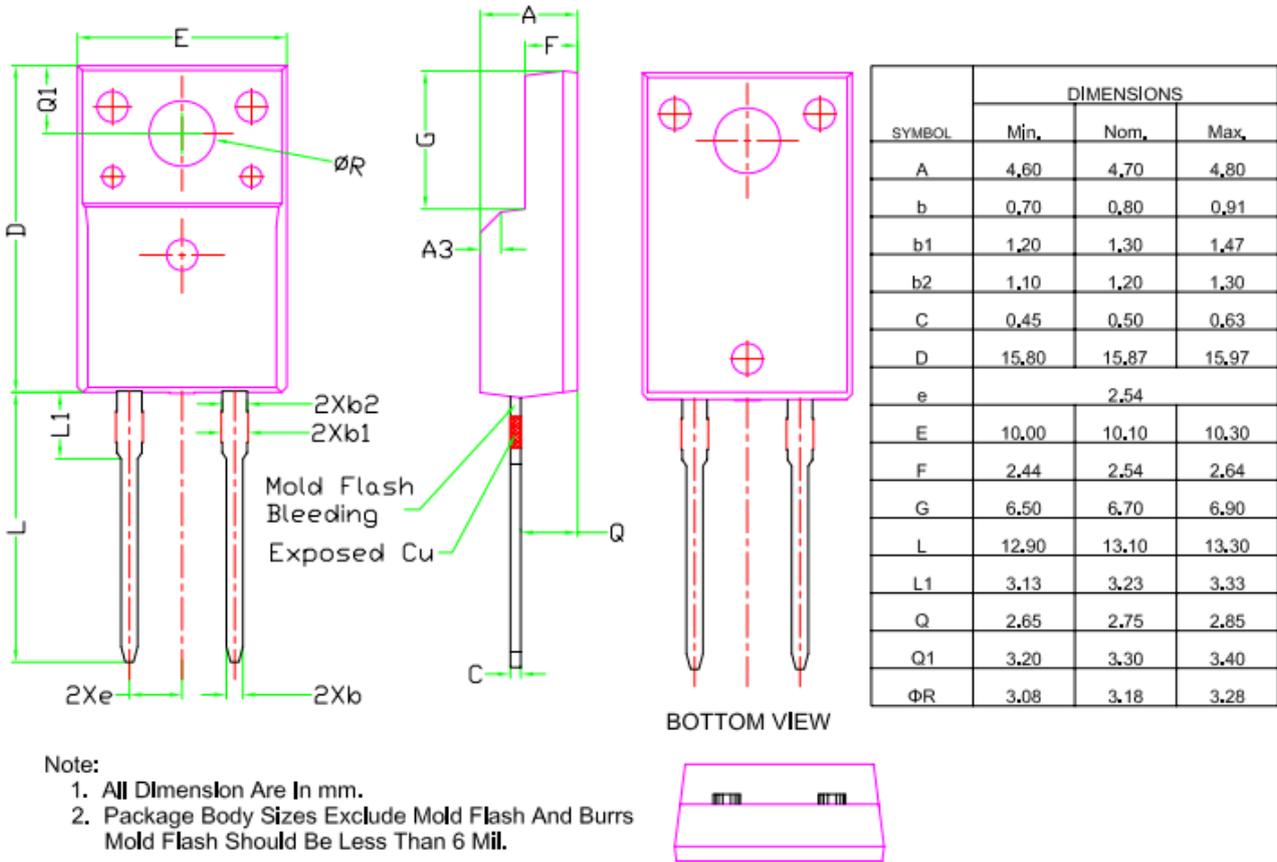


Figure 8. Transient Thermal Impedance

**Package Dimensions**



**Ordering Information**

Part Number	Marking	Package	Packaging Mode
G4S06515HT	G4S06515HT	TO-220F(SG)	50pcs/Tube

## Notes

- Global Power Technology reserves the right to change or modify any of the products and their inherent physical and technical specifications without prior notice.
- The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics.

## Related Links

- Global Power Technology Website: <http://www.globalpowertech.cn/>
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